Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Silicon Power
Schottky Diode

V_{RRM} = 20 V - 100 V

I_F = 35 A

Features
- High Surge Capability
- Types up to 100 V V_{RRM}

DO-4 Package

Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

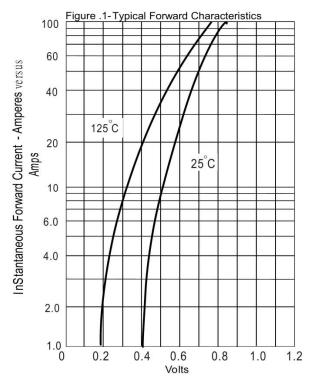| Parameter	Symbol	Conditions	MBR3520 (R)	MBR3530 (R)	MBR3535 (R)	MBR3540 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	T_C ≤ 110 °C	35	35	35	35	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_p = 8.3 ms	600	600	600	600	A
Operating temperature	T_j		-55 to 150	-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T_{stg}		-55 to 175	-55 to 175	-55 to 175	-55 to 175	°C

Electrical characteristics, at Tj = 25 °C, unless otherwise specified

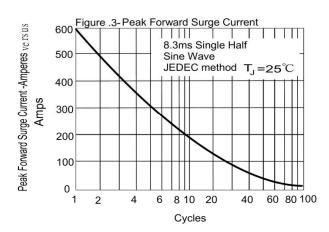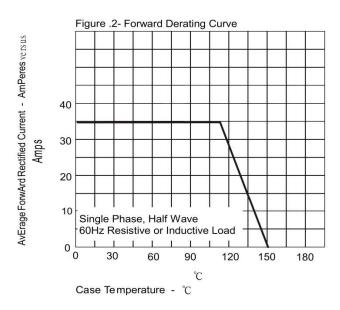| Parameter	Symbol	Conditions	MBR3520 (R)	MBR3530(R)	MBR3535 (R)	MBR3540 (R)	Unit
Diode forward voltage	V_F	I_F = 35 A, T_j = 25 °C	0.68	0.68	0.68	0.68	V
Reverse current	I_R	V_R = 20 V, T_j = 25 °C	1.5	1.5	1.5	1.5	mA
		V_R = 20 V, T_j = 125 °C	25	25	25	25	
Thermal characteristics							
Thermal resistance, junction - case	R_{thJC}		1.5	1.5	1.5	1.5	°C/W

Figure .1- Typical Forward Characteristics

InStantaneous Forward Current - Amperes versus Amps

125°C

25°C

Volts

Instantaneous Forward Voltage - Volts

Figure .2- Forward Derating Curve

AvErage FowArd Rectified Current - AmPeres versus Amps

Single Phase, Half Wave
60Hz Resistive or Inductive Load

Case Temperature - °C

Figure .3- Peak Forward Surge Current

Peak Forward Surge Current -Amperes versus Amps

8.3ms Single Half
Sine Wave
JEDEC method $T_J = 25°C$

Cycles

Number Of Cycles At 60Hz - Cycles

Figure .4-Typical Reverse Characteristics

Instantaneous Reverse Leakage Current - MillAmperes versus mAmps

$Tj = 175°C$

$Tj = 125°C$

$T_J = 75°C$

$T_J = 25°C$

Volts

Reverse Voltage - Volts